

BC856-8W

PNP Silicon Epitaxial Planar Transistor

Features

- Ideally suited for automatic insertion.
- Power dissipation.(PC=200mW)
- RoHS compliant package

Applications

- General purpose switching and amplification application

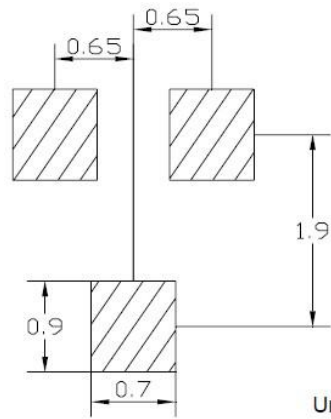
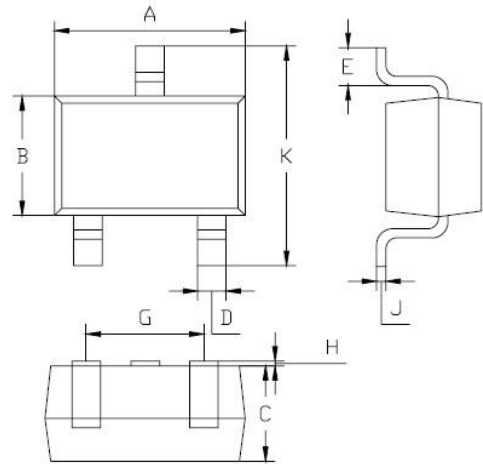
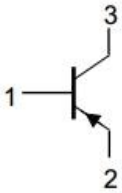
Packing & Order Information

3,000/Reel



RoHS
COMPLIANT

Graphic symbol



Unit : mm

SOT-323		
Dim	Min	Max
A	1.8	2.2
B	1.15	1.35
C	1.0Typical	
D	0.15	0.35
E	0.25	0.40
G	1.2	1.4
H	0.02	0.1
J	0.1Typical	
K	2.1	2.3
All Dimensions in mm		

ORDERING INFORMATION

Type No.	Marking	Package Code
BC856W	3As/3Bs	SOT-323
BC857W	3E/3F/3G	SOT-323
BC858W	3J/3K/3L	SOT-323

BC856-8W

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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

MAXIMUM Rating at 25 °C ambient temperature unless otherwise specified.

Symbol	Parameter	Value	Unit
VCBO	Collector-Base Voltage BC856W	-80	V
	BC857W	-50	
	BC858W	-30	
VCEO	Collector-Emitter Voltage BC856W	-65	V
	BC857W	-45	
	BC858W	-30	
VEBO	Emitter-Base Voltage	-5	V
IC	Collector Current -Continuous	-100	mA
PC	Collector Dissipation	200	mW
Tj,Tstg	Junction and Storage Temperature	-65 to +150	°C

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Parameter	Symbol	Conditions	Min	Max.	Units
Collector-base breakdown voltage	V(BR)CBO	IC=-10 μ A,IE=0 BC856W BC857W BC858W	-80 -50 -30		V
Collector-emitter breakdown voltage	V(BR)CEO	IC=-10mA,IB=0 BC856W BC857W BC858W	-65 -45 -30		V
Emitter-base breakdown voltage	V(BR)EBO	IE=-1 μ A,IC=0	-5		V
Collector cut-off current	ICBO	BC856W VCB=-70V,IE=0 BC857W VCB=-45V,IE=0 BC858W VCB=-25V,IE=0		-0.1	μ A
Collector cut-off current	ICEO	BC856W VCE=-60V,IB=0 BC857W VCE=-40V,IB=0 BC858W VCE=-25V,IB=0		-0.1	μ A
Emitter cut-off current	IEBO	VEB=-5V,IC=0 -0.1 μ A		-0.1	μ A
DC current gain	hFE	VCE=-5V,IC=-2mA BC856AW,BC857AW BC856BW,BC857BW,BC858BW BC857CW,BC858CW	125 220 420	250 475 800	

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Parameter	Symbol	Conditions	Min	Max.	Units
Collector-emitter saturation	VCE(sat)	IC=-100mA, IB= -5mA -0.5 mV		-0.5	mV
Base-emitter saturation voltage	VBE(sat)	IC=-100mA, IB= -5mA -1.1 V		-1.1	V
Transition frequency	fT	VCE=-5V,IC=-10mA,f=100MHz	100		MHz
Collector capacitance	CC	VCB=-10V,f=1MHz		4.5	pF

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